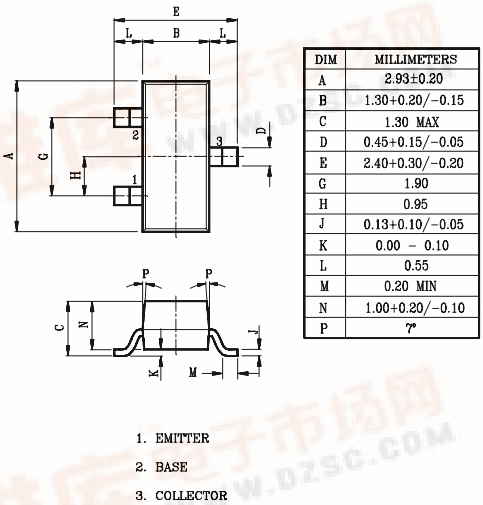
查询MMBTA517供应商 捷多邦，专业PCB打样工厂，24小时加急出货

KEC
KOREA ELECTRONICS CO.,LTD.

SEMICONDUCTOR
TECHNICAL DATA

MMBTA517
EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.



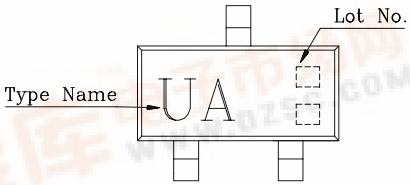
DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/−0.15
C	1.30 MAX
D	0.45+0.15/−0.05
E	2.40+0.30/−0.20
G	1.90
H	0.95
J	0.13+0.10/−0.05
K	0.00 − 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/−0.10
P	7°

SOT−23

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	400	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	−55～150	℃

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=0.1mA	40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=−1.0mA	10	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=40V	-	-	1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=10V	-	-	1	μA
DC Current Gain	h_{FE}	I_C=100mA, V_{CE}=2V	30K	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA, I_B=1mA	-	-	1	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=100mA, I_B=10mA	-	1.5	2	V
Current Gain Bandwidth Product	f_T	I_C=100mA, f=100MHz, V_{CE}=2V	-	220	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz	-	5	-	pF

*Pulse Test : Pulse Width≦300μS, Duty Cycle≦2.0%

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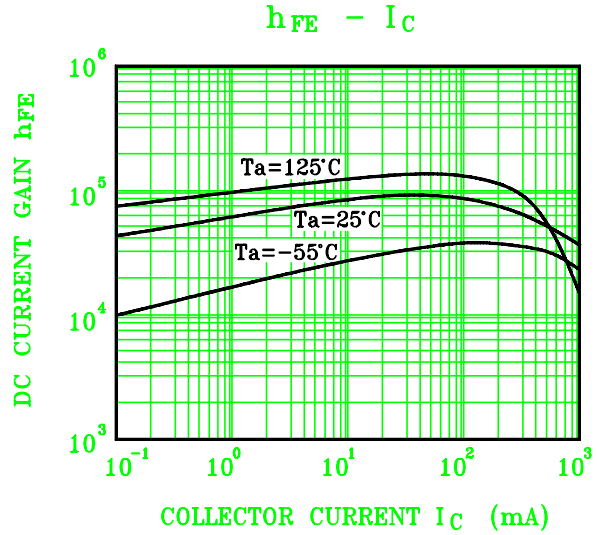
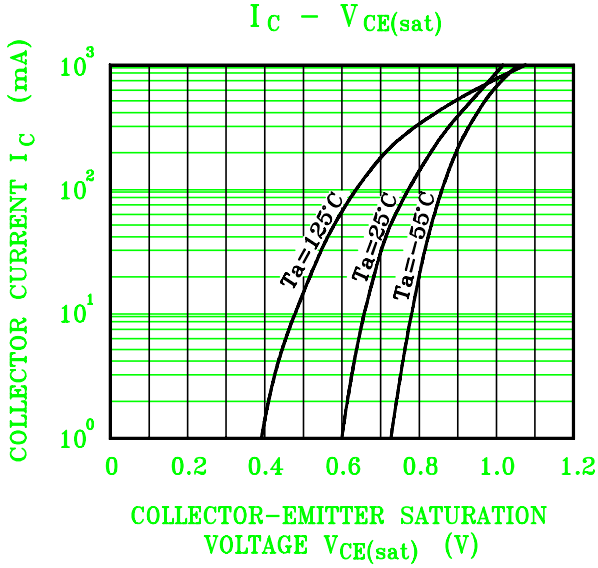
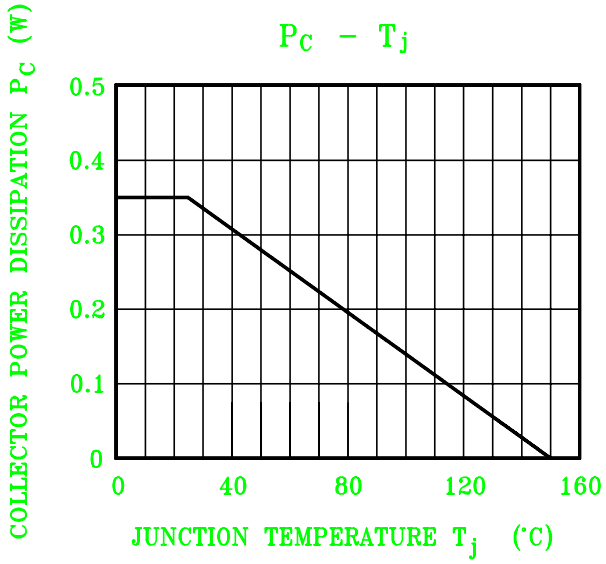
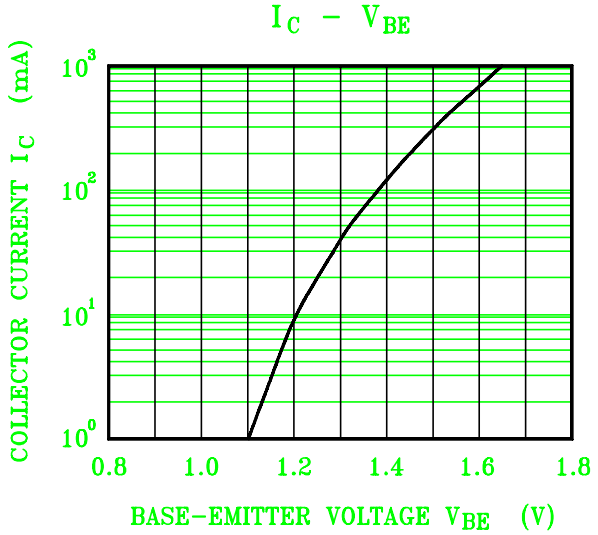

hFE – IC
DC CURRENT GAIN hFE
Ta=125°C
Ta=25°C
Ta=−55°C
COLLECTOR CURRENT IC (mA)


IC – VCE(sat)
COLLECTOR CURRENT IC (mA)
Ta=125°C
Ta=25°C
Ta=−55°C
COLLECTOR−EMITTER SATURATION VOLTAGE VCE(sat) (V)


PC – Tj
COLLECTOR POWER DISSIPATION PC (W)
JUNCTION TEMPERATURE Tj (°C)


IC – VBE
COLLECTOR CURRENT IC (mA)
BASE−EMITTER VOLTAGE VBE (V)